



**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

*BC*  
#25/E

*ba*  
11/6/03

**In re Application of:**

Pan et al.

**Serial No.:** 09/614,113

**Filed:** July 12, 2000

**For:** METHODS OF FORMING A GATE STACK THAT IS VOID OF SILICON CLUSTERS WITHIN A METALLIC SILICIDE FILM THEREOF (as amended)

**Confirmation No.:** 1710

**Examiner:** D. Deo

**Group Art Unit:** 1765

**Attorney Docket No.:** 2269-2915.3US  
(96-0149.02/US)

**Notice of Allowance Mailed:**

July 11, 2003

**Express Mail Mailing Label No.:** EV 326922977 US

**Date of Deposit with USPS:** October 9, 2003

**Person making Deposit:** Christopher Haughton

*Enter OIF X  
10/12/03  
11/21/03*

**AMENDMENT PURSUANT TO 37 C.F.R. § 1.312(a)**

Mail Stop ISSUE FEE  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

Please amend the above-referenced application as follows:

Amendments to the Title appear on page 3 of this paper.

**Match and Return**

**Amendments to the Specification appear on page 4 of this paper.**

**Amendments to the Claims are reflected in the listing of claims which begins on page 5 of this paper.**

**Amendments to the Drawings appear on page 8 of this paper and include both an attached replacement sheet and an annotated sheet showing changes.**

**Remarks begin on page 9 of this paper.**

**An Appendix including amended drawing figures is attached following page 9 of this paper.**

IN THE TITLE:

The title has been amended herein. Pursuant to 37 C.F.R. §§ 1.121 and 1.125 (as amended to date), please enter the title as amended.

~~TECHNIQUE FOR ELIMINATION OF PITTING ON  
SILICON SUBSTRATE DURING GATE STACK ETCH~~  
METHODS OF FORMING A GATE STACK THAT IS VOID OF  
SILICON CLUSTERS WITHIN A METALLIC SILICIDE FILM THEREOF